

### CE18U05P0G6

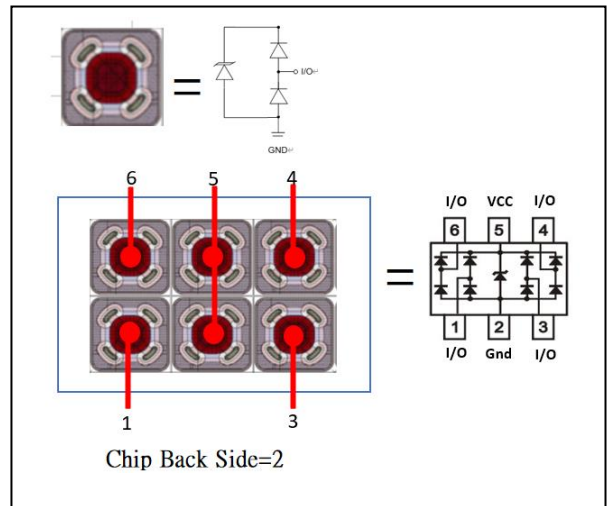
### 4-channel ultra low capacitance ESD diode

#### Wafer Information

Item	Description
Wafer Size	6 inch (150mm)
Wafer Thickness	150um ± 10um
Die Size (with scribe lane)	452um x 314um
Bond Pad Opening	68um x 68um
Scribe Lane Width	40um
Gross Die Per Wafer	112,000
Top Metal (for wire bond)	4μm AlSiCu
Backside Metal (for die bond)	Ag

- Complies with IEC 61000-4-2 standards:  
Contact discharge: ±20kV

#### Die Appearance



#### Circuit Diagram

#### Absolute Maximum Ratings ( $T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	56	W
Peak Pulse Current (8/20μs)	IPP	4	A
Operating Temperature Range	$T_J$	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +150	$^{\circ}\text{C}$

#### Electrical Characteristics ( $T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	VBR	6			V	$I_T = 1\text{mA}$
Reverse Leakage Current	IR			100	nA	VRWM = 5V
Forward voltage	VF			1.2	V	$I_F = 15\text{mA}$
Clamping Voltage	VC			10	V	IPP = 1A (8 x 20μs pulse)
Clamping Voltage	VC			14	V	IPP = 4A (8 x 20μs pulse)
Junction Capacitance	CJ		0.45	0.60	pF	VR = 0V, f = 1MHz

**Note:** Electrical parameters are only for die, performance may alter after assembly.